## 500 V, 150 mA NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor

# 2. Pinning information

Table 2. Pinning

Iddic 2.	· ····································		
Pin	Description	Simplified outline	Graphic symbol
1	base		
2	emitter	3	3 
3	collector	1 2	1 — 2
			svm021

# 3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
PMBTA45	-	plastic surface-mounted package; 3 leads	SOT23	

# 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
PMBTA45	LK*

- [1] \* = -: made in Hong Kong
  - \* = p: made in Hong Kong
  - \* = t: made in Malaysia
  - \* = W: made in China

# 5. Limiting values

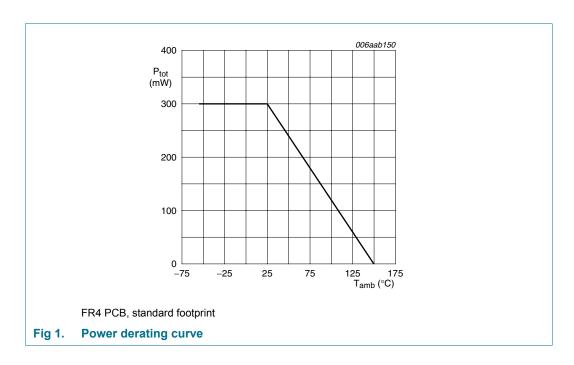
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{\text{CBO}}$	collector-base voltage	open emitter	-	500	V
$V_{CEO}$	collector-emitter voltage	open base	-	500	V
$V_{CESM}$	collector-emitter peak voltage	$V_{BE} = 0 V$	-	500	V
$V_{EBO}$	emitter-base voltage	open collector	-	6	V
I <sub>C</sub>	collector current		-	0.15	Α
I <sub>CM</sub>	peak collector current	$\begin{array}{l} \text{single pulse;} \\ t_p \leq 1 \text{ ms} \end{array}$	-	0.5	Α
I <sub>BM</sub>	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	200	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	<u>[1]</u> _	300	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		<b>–55</b>	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

500 V, 150 mA NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



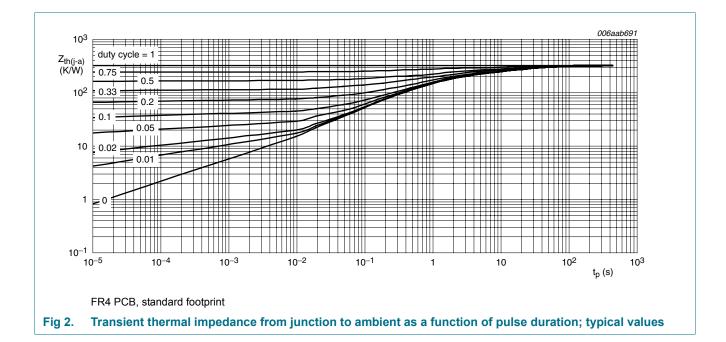
### 500 V, 150 mA NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor

### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	-	417	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	-	70	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



PMRTA45

## 500 V, 150 mA NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor

## 7. Characteristics

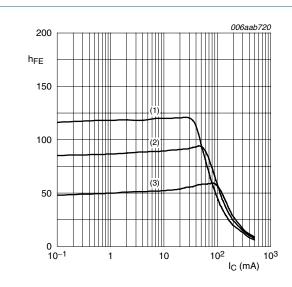
**Table 7. Characteristics** 

 $T_{amb}$  = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$I_{CBO}$		$V_{CB} = 360 \text{ V}; I_{E} = 0 \text{ A}$	-	-	100	nA
	current	$V_{CB} = 360 \text{ V; } I_E = 0 \text{ A;}$ $T_j = 150 \text{ °C}$	-	-	10	μΑ
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 360 V; V <sub>BE</sub> = 0 V	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_C = 0 \text{ A}$	-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 10 V				
		I <sub>C</sub> = 30 mA	50	100	-	
		I <sub>C</sub> = 50 mA	<u>[1]</u> 50	100	-	
OLOGI	collector-emitter	$I_C$ = 20 mA; $I_B$ = 2 mA	-	60	75	mV
	saturation voltage	I <sub>C</sub> = 50 mA; I <sub>B</sub> = 6 mA	[1] -	65	90	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C = 50 \text{ mA}; I_B = 5 \text{ mA}$	[1] _	0.75	0.9	V
f <sub>T</sub>	transition frequency	$V_{CE} = 10 \text{ V}; I_{E} = 10 \text{ mA};$ f = 100 MHz	-	35	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = 20 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	4	-	pF
C <sub>e</sub>	emitter capacitance	$V_{EB} = 0.5 \text{ V};$ $I_C = i_c = 0 \text{ A}; f = 1 \text{ MHz}$	-	200	-	pF
t <sub>d</sub>	delay time	$V_{CC}$ = 20 V; $I_{C}$ = 0.05 A;	-	80	-	ns
t <sub>r</sub>	rise time	I <sub>Bon</sub> = 5 mA; I <sub>Boff</sub> = -10 mA	-	2700	-	ns
t <sub>on</sub>	turn-on time		-	2780	-	ns
t <sub>s</sub>	storage time		-	3400	-	ns
t <sub>f</sub>	fall time		-	800	-	ns
t <sub>off</sub>	turn-off time		-	4200	-	ns

<sup>[1]</sup> Pulse test:  $t_p \leq 300~\mu s;~\delta \leq 0.02.$ 

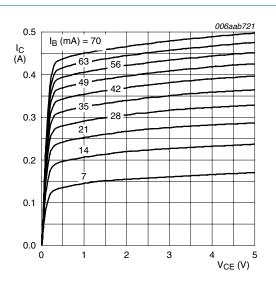
#### 500 V, 150 mA NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor



V<sub>CE</sub> = 10 V

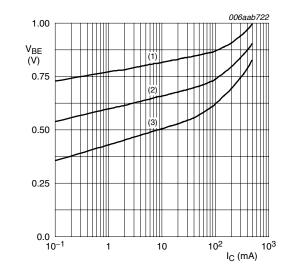
- (1)  $T_{amb} = 100 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = -55 \, ^{\circ}C$

Fig 3. DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$ 

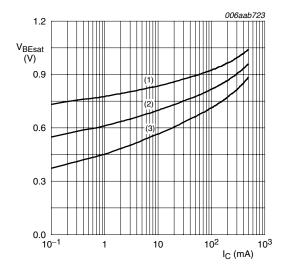
Fig 4. Collector current as a function of collector-emitter voltage; typical values



V<sub>CE</sub> = 10 V

- (1)  $T_{amb} = -55 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3) T<sub>amb</sub> = 100 °C

Fig 5. Base-emitter voltage as a function of collector current; typical values

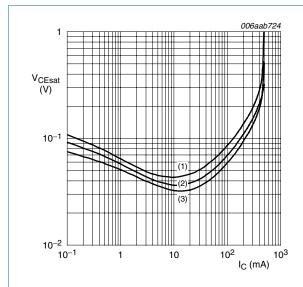


 $I_{\rm C}/I_{\rm B}=5$ 

- (1)  $T_{amb} = -55 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = 100 \, ^{\circ}C$

Fig 6. Base-emitter saturation voltage as a function of collector current; typical values

#### 500 V, 150 mA NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor



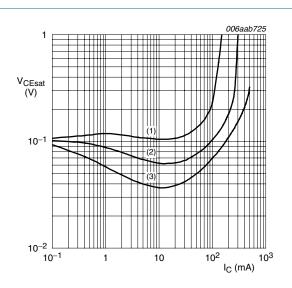
$$I_{\rm C}/I_{\rm B}=5$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



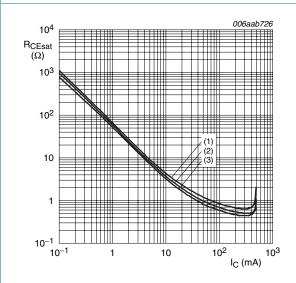
$$T_{amb}$$
 = 25 °C

(1) 
$$I_C/I_B = 20$$

(2) 
$$I_C/I_B = 10$$

(3)  $I_C/I_B = 5$ 

Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values



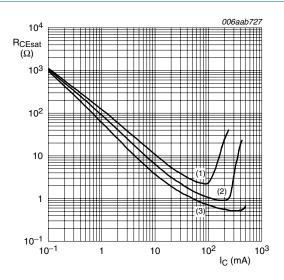
 $I_C/I_B = 5$ 

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 9. Collector-emitter saturation resistance as a function of collector current; typical values



(1) 
$$I_C/I_B = 20$$

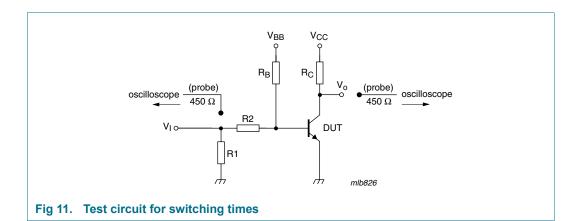
(2)  $I_C/I_B = 10$ 

(3)  $I_C/I_B = 5$ 

Fig 10. Collector-emitter saturation resistance as a function of collector current; typical values

500 V, 150 mA NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor

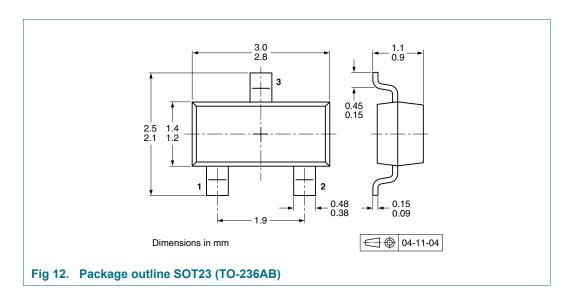
### 8. Test information



### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### 9. Package outline



# 10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			3000	10000
PMBTA45	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

[1] For further information and the availability of packing methods, see Section 14.

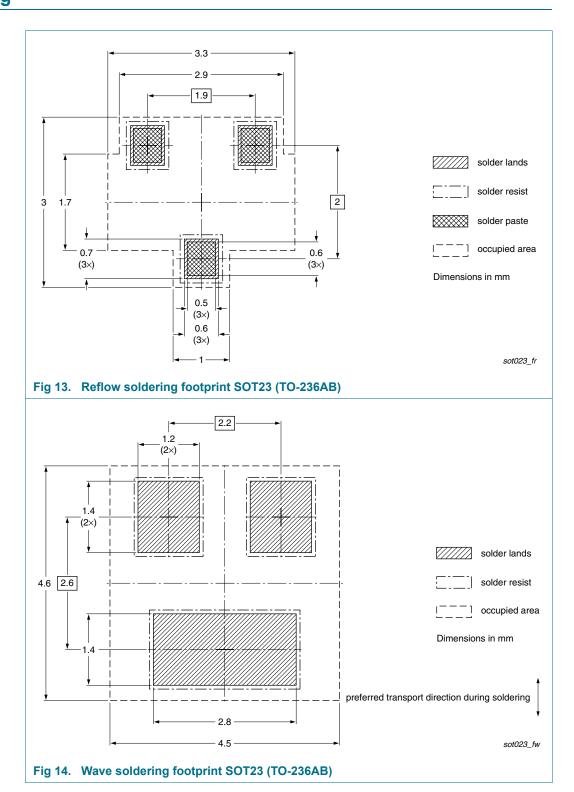
PMBTA45\_2

All information provided in this document is subject to legal disclaimers.

© NXP B.V. 2010. All rights reserved.

# 500 V, 150 mA NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor

# 11. Soldering



## 500 V, 150 mA NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor

# 12. Revision history

#### Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMBTA45_2	20100310	Product data sheet	-	PMBTA45_1
Modifications:	• Figure 7: upo	dated		
PMBTA45_1	20090916	Product data sheet	-	-

#### 500 V, 150 mA NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor

## 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.nxp.com">http://www.nxp.com</a>.

#### 13.2 Definitions

**Draft** — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

**Product specification** — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

#### 13.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of NXP Semiconductors.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use in automotive applications — This NXP Semiconductors product has been qualified for use in automotive applications. The product is not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on a weakness or default in the customer application/use or the application/use of customer's third party customer(s) (hereinafter both referred to as "Application"). It is customer's sole responsibility to check whether the NXP Semiconductors product is suitable and fit for the Application planned. Customer has to do all necessary testing for the Application in order to avoid a default of the Application and the product. NXP Semiconductors does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <a href="http://www.nxp.com/profile/terms">http://www.nxp.com/profile/terms</a>, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

**Export control** — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

**Quick reference data** — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

PMRTA45 2

All information provided in this document is subject to legal disclaimers.

© NXP B.V. 2010. All rights reserved.

PMBTA45 **NXP Semiconductors** 

500 V, 150 mA NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor

#### 13.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

### 14. Contact information

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: <a href="mailto:salesaddresses@nxp.com">salesaddresses@nxp.com</a>

## 500 V, 150 mA NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor

# 15. Contents

1	Product profile
1.1	General description
1.2	Features and benefits
1.3	Applications
1.4	Quick reference data 1
2	Pinning information 2
3	Ordering information 2
4	Marking 2
5	Limiting values 3
6	Thermal characteristics 4
7	Characteristics 5
8	Test information 8
8.1	Quality information
9	Package outline
10	Packing information 8
11	Soldering 9
12	Revision history
13	Legal information
13.1	Data sheet status
13.2	Definitions
13.3	Disclaimers
13.4	Trademarks 12
14	Contact information
15	Contents

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.